







SN74LXCH1T45 SCES939 - APRIL 2022

SN74LXCH1T45 Single-Bit Dual-Supply Bus Transceiver With Configurable Voltage Translation, 3-State Ouputs, and Bus-Hold Inputs

1 Features

- Fully configurable dual-rail design allows each port to operate from 1.1 V to 5.5 V
- Robust, glitch-free power supply sequencing
- Up to 420-Mbps support for 3.3 V to 5.0 V
- Bus hold on data inputs eliminates the need for external pull-up and pull-down resistors
- Schmitt-trigger control inputs allow for slow or noisy inputs
- Control inputs with integrated static pull-down resistors allow for floating control inputs
- High drive strength (up to 32 mA at 5 V)
- Low power consumption
 - 3-µA maximum (25°C)
 - 6-µA maximum (–40°C to 125°C)
- V_{CC} isolation and V_{CC} disconnect feature
 - If either V_{CC} supply is < 100 mV all I/O's become high-impedance
 - I_{off-float} supports V_{CC} disconnect operation
- I_{off} supports partial-power-down mode operation
- Compatible with LVC family level shifters
- Control logic (DIR) are referenced to V_{CCA}
- Operating temperature from -40°C to +125°C
- Latch-up performance exceeds 100 mA per JESD 78, class II
- ESD protection exceeds JESD 22
 - 4000-V human-body model
 - 1000-V charged-device model

2 Applications

- Eliminate slow or noisy input signals
- **Driving indicator LEDs or buzzers**
- Debouncing a mechanical switch
- General purpose I/O level shifting

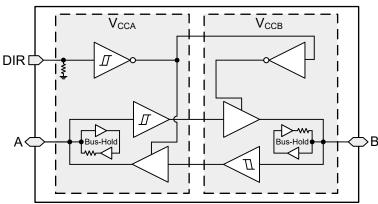
3 Description

The SN74LXCH1T45 is an 1-bit, dual-supply noninverting bidirectional voltage level translation device with bus-hold circuitry. The I/O pin A and control pin (DIR) are referenced to V_{CCA} logic levels, and the I/O pin B is referenced to V_{CCB} logic levels. The A pin is able to accept I/O voltages ranging from 1.1 V to 5.5 V, while the B port can accept I/O voltages from 1.1 V to 5.5 V. A high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A. See Device Functional Modes for a summary of the operation of the control logic.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
	SC70 (DCK) (6)	2.00 mm × 1.25 mm
SN74LXCH1T45	SON (DRY) (6)	1.45 mm × 1.00 mm
	X2SON (DTQ) (6)	1.00 mm × 0.80 mm

For all available packages, see the orderable addendum at the end of the data sheet.



Note: Bus-hold circuits are only present for data inputs, not control inputs

Functional Block Diagram



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4 Revision History

DATE	REVISION	NOTES
April 2022	*	Initial Release



5 Pin Configuration and Functions

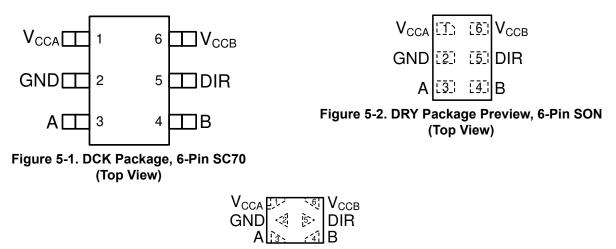


Figure 5-3. DTQ Package Preview, 6-Pin X2SON Transparent (Top View)

Table 5-1. Pin Functions

	PIN	TYPE(1)	DESCRIPTION						
NAME	NO.	ITPE(')	DESCRIPTION						
A	3 I/O Input or output A. Referenced to V _{CCA} .								
В	4	I/O	Input or output B. Referenced to V _{CCB} .						
DIR	5	I	Direction-control signal for all ports. Referenced to V _{CCA} .						
GND	2	_	Ground.						
DIR	5	I	Direction-control signal for all ports. Referenced to V _{CCA} .						
V _{CCA}	1	_	A-port supply voltage. 1.1 V \leq V _{CCA} \leq 5.5 V.						
V _{CCB}	6	_	B-port supply voltage. 1.1 V \leq V _{CCB} \leq 5.5 V.						

(1) I = input, O = output, GND = ground



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

	3 1 3 ()		MIN	MAX	UNIT
V _{CCA}	Supply voltage A		-0.5	6.5	V
V _{CCB}	Supply voltage B		-0.5	6.5	V
		I/O Ports (A Port)	-0.5	6.5	
VI	Input Voltage ⁽²⁾	I/O Ports (B Port)	-0.5	6.5	V
		Control Inputs	-0.5	6.5	
.,	Voltage applied to any output in the high-impedance or power-off	A Port	-0.5	6.5	
Vo	state ⁽²⁾	B Port	-0.5	6.5	V
V	Voltage applied to any output in the high or law state(2) (3)	A Port	-0.5	V _{CCA} + 0.5	V
Vo	Voltage applied to any output in the high or low state ^{(2) (3)}	B Port	-0.5	$\frac{V_{CCA} + 0.5}{V_{CCB} + 0.5}$	\ \ \
I _{IK}	Input clamp current	V _I < 0	-50		mA
I _{OK}	Output clamp current	V _O < 0	-50		mA
Io	Continuous output current		-50	50	mA
	Continuous current through V _{CC} or GND		-200	200	mA
Tj	Junction Temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure beyond the limits listed in Recommended Operating Conditions. may affect device reliability.

- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 6.5 V maximum if the output current rating is observed.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

				MIN	MAX	UNIT		
V _{CCA}	Supply voltage A			1.1	5.5	V		
V _{CCB}	Supply voltage B			1.1	5.5	V		
			V _{CCI} = 1.1 V - 1.3 V	V _{CCI} x 0.8				
		Data Inputs	V _{CCI} = 1.4 V - 1.95 V	V _{CCI} x 0.65				
V_{IH}	High-level input voltage	(A,B)	V _{CCI} = 2.3 V - 2.7 V	1.7		V		
	vollago	(Referenced to V _{CCI})	2					
			V _{CCI} x 0.7					
			V _{CCI} = 1.1 V - 1.3 V		V _{CCI} x 0.2			
	Low-level input voltage (A,B) $(Referenced to V_{CCI})$ $V_{CCI} = 2.3 \text{ V} - 2.7$ $V_{CCI} = 3.0 \text{ V} - 3.6$		V _{CCI} = 1.4 V - 1.95 V		V _{CCI} x 0.35			
V_{IL}			V _{CCI} = 2.3 V - 2.7 V		0.7	V		
			V _{CCI} = 3.0 V - 3.6 V		0.8			
			V _{CCI} = 4.5 V - 5.5 V		V _{CCI} x 0.3			
			V _{CCO} = 1.1 V		-0.1			
			V _{CCO} = 1.4 V		-4			
ı	High-level output o	urront	V _{CCO} = 1.65 V		-8	mA		
l _{OH}	i ligit-level output c	unent	V _{CCO} = 2.3 V		-12	ШД		
			V _{CCO} = 3 V		-24			
			V _{CCO} = 4.5 V		-32			
			V _{CCO} = 1.1 V		0.1			
			V _{CCO} = 1.4 V		4			
l ₋ .	Low-level output c	urront	V _{CCO} = 1.65 V		8	mA		
l _{OL}	Low-level output c	unent	$V_{CCO} = 2.3 \text{ V}$		12	ШД		
			V _{CCO} = 3 V		24			
				32				
VI	Input voltage			0	5.5	V		
Vo	Output voltage	Active State		0	V _{CCO}	V		
• 0	Output voitage	Tri-State		0	5.5	v		
T _A	Operating free-air	temperature		-40	125	°C		

⁽¹⁾ V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port.

6.4 Thermal Information

		SN74LXCH1T45							
	THERMAL METRIC ⁽¹⁾	DCK (SC70)	DRY (SON)	DTQ (X2SON)	UNIT				
		6 PINS	6 PINS	6 PINS					
R _{θJA}	Junction-to-ambient thermal resistance	205.2	293.4	285.0	°C/W				
R _{θJC(top)}	Junction-to-case (top) thermal resistance	132.4	184.0	140.0	°C/W				
$R_{\theta JB}$	Junction-to-board thermal resistance	65.1	164.9	208.5	°C/W				
Y _{JT}	Junction-to-top characterization parameter	48.0	28.3	6.1	°C/W				
Y_{JB}	Junction-to-board characterization parameter	64.9	164.0	207.8	°C/W				
$R_{\theta JC(bottom)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W				

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics app report.



6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)(1) (2)

PARAMETER T						0	peratir	ng free	-air tempera	ture (T	۵)	
PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}		25°C		–40°	C to 85°C	-40°	C to 125°C	UNI
					MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP MAX	
			1.1 V	1.1 V				0.44	0.88	0.44	0.88	
			1.4 V	1.4 V				0.60	0.98	0.60	0.98	
	Positive-	Control Inputs	1.65 V	1.65 V				0.76	1.13	0.76	1.13	
V_{T+}	going input- threshold	(DIR)	2.3 V	2.3 V				1.08	1.56	1.08	1.56	V
	voltage	(Referenced to V _{CCI})	3 V	3 V				1.48	1.92	1.48	1.92	
			4.5 V	4.5 V				2.19	2.74	2.19	2.74	
			5.5 V	5.5 V				2.65	3.33	2.65	3.33	
			1.1 V	1.1 V				0.17	0.48	0.17	0.48	
			1.4 V	1.4 V				0.28	0.59	0.28	0.59	
	Negative-	Control Inputs	1.65 V	1.65 V				0.35	0.69	0.35	0.69	
V _{T-}	going input- threshold	(DIR)	2.3 V	2.3 V				0.56	0.97	0.56	0.97	V
	voltage	(Referenced to V _{CCI})	3 V	3 V				0.89	1.5	0.89	1.5	
			4.5 V	4.5 V				1.51	1.97	1.51	1.97	
			5.5 V	5.5 V				1.88	2.4	1.88	2.4	
			1.1 V	1.1 V				0.2	0.4	0.2	0.4	
			1.4 V	1.4 V				0.25	0.5	0.25	0.5	
	Input- threshold hysteresis (V _{T+} – V _{T-})	Control Input	1.65 V	1.65 V				0.3	0.55	0.3	0.55	
ΔV_T		(DIR) (Referenced to V _{CCA})	2.3 V	2.3 V				0.38	0.65	0.38	0.65	V
			3 V	3 V				0.46	0.72	0.46	0.72	
			4.5 V	4.5 V				0.58	0.93	0.58	0.93	
			5.5 V	5.5 V				0.69	1.06	0.69	1.06	
		I _{OH} = -100 μA	1.1V – 5.5V	1.1V – 5.5V				V _{CCO} - 0.1		V _{CCO} - 0.1		
	Lligh lovel	I _{OH} = -4 mA	1.4 V	1.4 V				1		1		
V_{OH}	High-level output	I _{OH} = -8 mA	1.65 V	1.65 V				1.2		1.2		V
0	voltage (3)	I _{OH} = -12 mA	2.3 V	2.3 V				1.9		1.9		
		I _{OH} = -24 mA	3 V	3 V				2.4		2.4		1
		I _{OH} = -32 mA	4.5 V	4.5 V				3.8		3.8	,	
		I _{OL} = 100 μA	1.1V – 5.5V	1.1V - 5.5V					0.1		0.1	
		I _{OL} = 4 mA	1.4 V	1.4 V					0.3		0.3	
.,	Low-level	I _{OL} = 8 mA	1.65 V	1.65 V					0.45		0.45	
V _{OL}	output voltage ⁽⁴⁾	I _{OL} = 12 mA	2.3 V	2.3 V					0.3		0.3	V
		I _{OL} = 24 mA	3 V	3 V					0.55		0.55	
		I _{OL} = 32 mA	4.5 V	4.5 V					0.55		0.55	
		V _I = 0.39	1.1 V	1.1 V				4		4		
	Bus-hold low	V _I = 0.49	1.4 V	1.4 V				15		10		1
	sustaining	V _I = 0.58	1.65 V	1.65 V				25		20		1 .
I _{BHL}	current Port A or Port	V _I = 0.70	2.3 V	2.3 V				45		45		μA
	B (6)	V _I = 0.80	3 V	3 V				75		75		
		V _I = 1.35	4.5 V	4.5 V				100		100		



over operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

PARAMETER						0	peratir	ng free	air temp	eratı	ure (T _A)		
PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}		25°C		–40°	C to 85°C	;	–40°0	C to 12	25°C	UNI
					MIN	TYP	MAX	MIN	TYP M	AX	MIN	TYP	MAX	
		V _I = 0.71 V	1.1 V	1.1 V						-4			-4	
	Bus-hold high	V _I = 0.91 V	1.4 V	1.4 V					_	-15			-15	
ı	current	V _I = 1.07 V	1.65 V	1.65 V					_	-25			-25	<u></u>
внн	Port A or Port	V _I = 1.70 V	2.3 V	2.3 V				,	_	45			-4 5	μA
	B ⁽⁷⁾	V _I = 2.00 V	3 V	3 V					_	-75			-75	
		V _I = 3.15 V	4.5 V	4.5 V					-1	00			-100	
			1.3 V	1.3 V						75			75	
			1.6 V	1.6 V					1	25			125	
	Bus-hold low	Ramp input up	1.95 V	1.95 V					2	200			200	١.,
ВНГО	overdrive current (8)	$V_I = 0$ to V_{CCI}	2.7 V	2.7 V					3	800			300	μA
			3.6 V	3.6 V					5	500			500	
			5.5 V	5.5 V					S	000			900	
			1.3 V	1.3 V				-75			-75			
			1.6 V	1.6 V				-125			-125			
	Bus-hold high	Ramp input down	1.95 V	1.95 V				-200			-200			_
внно	overdrive current (9)	$V_I = V_{CCI}$ to 0	2.7 V	2.7 V				-300			-300			μA
	Current		3.6 V	3.6 V				-500			-500			
			5.5 V	5.5 V				-900			-900	-		
	Input leakage	Control input (DIR) V _I = V _{CCA} or GND	1.1V – 5.5V	1.1V – 5.5V	-0.1		1	-0.1		2	-0.1		2	μÆ
l _I	current	Data Inputs ⁽⁵⁾ (Ax, Bx) V _I = V _{CCI} or GND	1.1V – 5.5V	1.1V – 5.5V	-0.3		1	-1		1	-2		2	μA
	Partial power	A Port or B Port	0 V	0 V - 5.5 V	-1		1	-2		2	-2.5		2.5	
l _{off}	down current	V _I or V _O = 0 V - 5.5 V	0 V - 5.5 V	0 V	-1		1	-2		2	-2.5		2.5	μA
	Floating	V	Floating (10)	0 V - 5.5 V	-1.5		1.5	-2		2	-2.5		2.5	
off-float	supply Partial power down current	A Port or B Port V _I or V _O = GND	0 V - 5.5 V	Floating (10)	-1.5		1.5	-2		2	-2.5		2.5	μÆ
			1.1V – 5.5V	1.1V – 5.5V			2			2		-	4	
		$V_I = V_{CCI}$ or GND	0 V	5.5 V	-0.2			-0.5			-1			
CCA	V _{CCA} supply current	I _O = 0	5.5 V	0 V			1			1			2	μA
	Current	V _I = GND I _O = 0	5.5 V	Floating (10)			1.5			1.5			2	
			1.1V – 5.5V	1.1V - 5.5V			2			2			4	
		$V_I = V_{CCI}$ or GND $I_O = 0$	0 V	5.5 V			1			1			2	
ССВ	V _{CCB} supply current	10 - 0	5.5 V	0 V	-0.2			-0.5			-1	-		μΑ
	V	V _I = GND I _O = 0	Floating (10)	5.5 V			1.5			1.5			2	
ICCA +	Combined supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	1.1V – 5.5V	1.1V – 5.5V			3			4			6	μÆ



over operating free-air temperature range (unless otherwise noted)(1) (2)

						0	peratir	ng free	-air te	mperat	ure (T)		
PA	RAMETER	TEST CONDITIONS	V _{CCA}	V _{CCB}		25°C		-40 °	°C to 8	5°C	-40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
ΔI _{CCA}	V _{CCA} additional supply	Control input (DIR): V _I = V _{CCA} - 0.6 V A port = VCCA or GND B Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	μA
	current per input	A Port: $V_I = V_{CCA} - 0.6 V$ DIR = V_{CCA} , B Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	
ΔI _{CCB}	V _{CCB} additional supply current per input	B Port: V _I = V _{CCB} - 0.6 V DIR = GND, A Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	μА
C _i	Control Input Capacitance	V _I = 3.3 V or GND	3.3 V	3.3 V		2.2				4			4	pF
C _{io}	Data I/O Capacitance	V _{CCO} = 0V V _O = 1.65V DC +1 MHz -16 dBm sine wave	3.3 V	3.3 V		4.9				10			7	pF

- (1)
- V_{CCI} is the V_{CC} associated with the input port V_{CCO} is the V_{CC} associated with the output port (2)
- (3) Tested at $V_I = V_{T+(MAX)}$
- Tested at $V_I = V_{T-(MIN)}$ For I/O ports, the parameter I_I includes the I_{OZ} current (4) (5)
- I_{BHL} should be measured after lowering V_{I} to GND and then raising it to the defined input voltage (6)
- I_{BHH} should be measured after raising V_{I} to V_{CCI} and then lowering it to the defined input voltage An external driver must source at least I_{BHLO} to switch this node from low-to-high (7)
- (8)
- An external driver must sink at least I_{BHHO} to switch this node from high to low
- (10) Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA

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6.6 Switching Characteristics, $V_{CCA} = 1.2 \pm 0.1 \text{ V}$

									B-Port S	Supply	Voltage (V _{CC}	:B)											
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0.1	٧	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	: V	3.3 ± 0.3	3 V	5.0 ± 0.	.5 V	UNIT						
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX							
		Α	В	-40°C to 85°C	6	85	4	41	3	36	1	33	1	34	1	44							
	Propagation			-40°C to 125°C	8	55	6	37	5	33	3	30	3	30	2	33							
t _{pd}	delay	В	Α	-40°C to 85°C	6	85	5	71	4	67	3	60	3	57	3	58	ns						
		Ь	A	-40°C to 125°C	8	55	6	47	6	43	5	38	4	37	4	36							
		DIR	Α	-40°C to 85°C	5	53	5	53	5	53	5	53	5	53	4	53							
	Disable time		^	-40°C to 125°C	7	47	7	47	7	47	7	47	7	47	7	47							
t _{dis}	Disable time	DIR	R B	-40°C to 85°C	10	85	7	47	6	41	5	34	5	33	4	32	ns						
			DIR	DIR	DIR	В	-40°C to 125°C	14	71	11	48	10	41	8	34	8	33	6	32				
			DIR A	_	-40°C to 85°C	21	150	17	110	16	99	13	86	13	83	12	85						
				DIR	DIR	DIR	DIR	DIR	DIR	DIR	R A	-40°C to 125°C	27	121	23	89	21	80	17	68	17	65	15
t _{en}			Enable time		DIP		Ь	-40°C to 85°C	16	118	14	89	13	84	12	81	11	82	11	92	ns		
			-40°C to 125°C	19	97	18	79	17	73	16	68	15	67	14	70								



6.7 Switching Characteristics, $V_{CCA} = 1.5 \pm 0.1 \text{ V}$

	DADAMETED								B-Port S	Supply	Voltage (V _{CC}	в)					
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0.1	٧	1.5 ± 0.1	٧	1.8 ± 0.1	5 V	2.5 ± 0.2	: V	3.3 ± 0.3	3 V	5.0 ± 0.	5 V	UNIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	
		Α	В	-40°C to 85°C	1	70	1	29	1	24	1	20	1	19	1	19	
	Propagation			-40°C to 125°C	1	46	1	29	1	24	1	21	1	19	1	20	ns
t _{pd}	delay	В	Α	-40°C to 85°C	1	39	1	29	1	26	1	23	1	21	1	21	1115
		В	A	-40°C to 125°C	1	36	1	29	1	26	1	23	1	21	1	21	
		DIR	Α	-40°C to 85°C	3	29	3	29	3	29	3	29	3	29	3	29	
	Disable time	DIK	A	-40°C to 125°C	5	29	5	29	5	29	5	29	5	29	5	29	
t _{dis}	Disable time	DIR	В	-40°C to 85°C	11	78	8	45	7	38	5	31	5	30	4	28	ns
		DIK	Р	-40°C to 125°C	15	70	14	46	11	40	10	32	9	31	8	29	
		DID	_	-40°C to 85°C	19	113	15	69	13	59	11	49	11	46	9	44	
	Enable times	DIR A	A	-40°C to 125°C	27	101	23	70	21	61	18	51	17	48	15	45	
t _{en}	Enable time	nable time	В	-40°C to 85°C	12	91	10	53	9	48	8	43	8	41	7	41	ns
	DIR	В	-40°C to 125°C	16	71	14	54	13	49	12	44	12	42	11	42		



6.8 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15 \text{ V}$

	DADAMETED								B-Port S	Supply	Voltage (V _{CC}	в)					
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0.1	V	1.5 ± 0.1	٧	1.8 ± 0.1	5 V	2.5 ± 0.2	٧	3.3 ± 0.3	3 V	5.0 ± 0.	5 V	UNIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	
		A	В	-40°C to 85°C	1	66	1	26	1	21	1	17	1	16	1	15	
	Propagation	^		-40°C to 125°C	1	43	1	27	1	22	1	18	1	17	1	16	
t _{pd}	delay	В	Α	-40°C to 85°C	1	35	1	24	1	21	1	18	1	17	1	17	ns
		Ь	^	-40°C to 125°C	1	32	1	24	1	22	1	19	1	18	1	17	
	D	DIR	Α	-40°C to 85°C	2	22	2	22	2	23	2	23	2	22	2	22	
	Disable time	DIK	^	-40°C to 125°C	4	23	4	31	4	23	4	23	4	23	4	23	
t _{dis}	Disable time	DIR	В	-40°C to 85°C	9	73	7	40	6	34	4	27	4	25	3	23	ns
		DIK		-40°C to 125°C	15	64	13	42	11	36	6	28	8	27	6	25	
		DID	Α	-40°C to 85°C	17	103	13	59	12	50	9	40	9	38	7	35	
	Enable time	DIK	A	-40°C to 125°C	23	90	21	61	19	53	16	43	12	39	12	37	
t _{en}		DIB	ь	-40°C to 85°C	11	80	9	44	8	39	7	34	6	33	6	32	ns
		DIR B	В	-40°C to 125°C	14	61	12	45	11	40	10	36	10	34	9	35	



6.9 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2 \text{ V}$

See Figure 7-1 and Table 7-1 for test circuit and loading. See Figure 7-2, Figure 7-3, and Figure 7-4 for measurement waveforms.

	DADAMETED EDG								B-Port	Supply	Voltage (V _{CC}	:в)										
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0	.1 V	1.5 ± 0.1	I V	1.8 ± 0.1	5 V	2.5 ± 0.2	2 V	3.3	3 ± 0.3 V	5.	.0 ± 0.5	٧	UNIT				
					MIN TYF	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX					
		Α	В	-40°C to 85°C	1	59	1	23	1	19	1	15	1	13	1		12					
	Propagation			-40°C to 125°C	1	38	1	23	1	19	1	15	1	14	1		13	ns				
t _{pd}	delay	В	^	-40°C to 85°C	1	32	1	20	1	17	1	15	1	14	1		13	115				
		В	A	-40°C to 125°C	1	29	1	21	1	18	1	15	1	14	1		14					
		DIR	DIR	Α	-40°C to 85°C	1	16	1	23	1	16	1	16	1	20	1		16				
	Disable time	DIIX	^	-40°C to 125°C	2	16	2	16	2	16	2	25	2	16	2		16	ns				
t _{dis}	Disable time	DIB	В	DIR B	-40°C to 85°C	8	63	6	35	5	29	3	23	3	22	2		19	115			
		DIK		-40°C to 125°C	13	56	10	37	10	31	8	25	7	23	5		20					
				DIR	DIR	DIR	^	-40°C to 85°C	14	91	11	49	10	41	8	33	7	30	6		27	
	Enable time			Α	-40°C to 125°C	21	76	18	51	16	44	14	35	13	32	10		29	ns			
t _{en}	n Enable time DIR B	DIP	В	-40°C to 85°C	8	67	6	33	5	33	4	25	4	24	4		23	115				
		DIR E	D	-40°C to 125°C	11	49	9	34	8	30	7	27	7	27	6		24					

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6.10 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3 V$

	DADAMETED EDOM							B-Port S	Supply	Voltage (V _{CC}	в)										
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0.	1 V	1.5 ± 0.1	٧	1.8 ± 0.1	5 V	2.5 ± 0.2	: V	3.3 ± 0.3	3 V	5.	0 ± 0.5	V	UNIT			
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP	MAX				
		Α	В	-40°C to 85°C	1	57	1	21	1	17	1	14	1	12	1		11				
	Propagation			-40°C to 125°C	1	36	1	22	1	18	1	14	1	13	1		12	ns			
t _{pd}	delay	В	Α	-40°C to 85°C	1	33	1	19	1	16	1	13	1	12	1		12	115			
		В	^	-40°C to 125°C	1	29	1	19	1	17	1	14	1	13	1		12				
		DIR	Α	-40°C to 85°C	1	14	1	14	1	14	1	14	1	20	1		14				
	Disable time	DIIX	^	-40°C to 125°C	1	34	1	15	1	15	1	15	1	15	1		17	ns			
t _{dis}	Disable time	DIR B	DIR	Р	-40°C to 85°C	7	59	5	32	5	27	3	21	3	20	2		18	115		
		DIK		-40°C to 125°C	12	52	9	33	9	29	7	23	7	22	5		19				
	DIB				DIR	_	-40°C to 85°C	13	86	10	44	9	37	7	30	7	28	5		25	
	Enable time				^	-40°C to 125°C	19	71	16	46	14	39	12	32	12	29	10		26	ns	
t _{en}	Enable time DIR	DIP	B	-40°C to 85°C	8	64	6	30	5	27	4	23	4	22	3		22	110			
		DIR B	В	-40°C to 125°C	10	46	9	31	8	28	7	24	6	23	6		22				



6.11 Switching Characteristics, $V_{CCA} = 5.0 \pm 0.5 \text{ V}$

See Figure 7-1 and Table 7-1 for test circuit and loading. See Figure 7-2, Figure 7-3, and Figure 7-4 for measurement waveforms.

									B-Port S	Supply	Voltage (V _{CC}	в)						
	PARAMETER	FROM	то	Test Conditions	1.2 ± 0.1	٧	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	: V	3.3 ± 0.3	3 V	5.	0 ± 0.5 V	UN	NIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP M	λX	
		Α	В	-40°C to 85°C	1	57	1	21	1	17	1	13	1	12	1		11	
	Propagation	A		-40°C to 125°C	1	36	1	21	1	17	1	14	1	12	1		11	
t _{pd}	delay	В	^	-40°C to 85°C	1	47	1	19	1	15	1	12	1	11	1		11 "	ns
		В	Α	-40°C to 125°C	1	33	1	20	1	16	1	13	1	12	1		11	
	DIR	DIB	Α	-40°C to 85°C	1	12	1	12	1	21	1	12	1	15	1		12	
	Disable time	DIK	^	-40°C to 125°C	1	12	1	12	1	20	1	12	1	12	1		12	ns
t _{dis}	Disable time	DIR	В	-40°C to 85°C	1	57	1	30	4	25	3	20	3	19	2		17 ''	15
		DIK	В	-40°C to 125°C	11	50	9	31	8	27	6	21	6	20	4		18	
		DIB	Α	-40°C to 85°C	8	98	6	42	8	34	7	27	7	25	5		23	
	Final Latina		^	-40°C to 125°C	18	73	15	44	13	36	11	29	11	27	9		24	
t _{en}	Enable time	DIR	В	-40°C to 85°C	6	62	4	28	3	24	3	20	2	19	2		18	ns
	D	DIK	0	-40°C to 125°C	9	43	7	28	6	25	5	21	4	20	4		19	

Product Folder Links: SN74LXCH1T45



6.12 Switching Characteristics: T_{sk}, T_{MAX}

over operating free-air temperature range (unless otherwise noted)

						ting fre		
PARAMETER	TEST CO	NDITIONS	V _{CCI}	V _{cco}	-40°	C to 12	5°C	UNIT
					MIN	TYP	MAX	
			3.0 V – 3.6 V	4.5 V – 5.5 V	200	420		
			2.25 V - 2.75 V	4.5 V - 5.5 V	150	300		
			1.65 V – 1.95 V	4.5 V – 5.5 V	100	200		
		Up Translation	1.1 V – 1.3 V	4.5 V – 5.5 V	20	40		
	50% Duty Cycle		1.65 V – 1.95 V	3.0 V – 3.6 V	100	210		
	Input One channel		1.1 V – 1.3 V	3.0 V – 3.6 V	10	20		
T _{MAX} - Maximum	switching		1.1 V – 1.3 V	1.65 V – 1.95 V	5	10		Mhna
Data Rate	20% of pulse >		4.5 V – 5.5 V	3.0 V – 3.6 V	100	210		Mbps
	0.7*V _{CCO} 20% of pulse <		4.5 V – 5.5 V	2.25 V - 2.75 V	75	140		
	0.3*V _{CCO}		4.5 V – 5.5 V	1.65 V – 1.95 V	50	75		
		Down Translation	4.5 V – 5.5 V	1.1 V – 1.3 V	15	30		
			3.0 V – 3.6 V	1.65 V – 1.95 V	40	75		
			3.0 V – 3.6 V	1.1 V – 1.3 V	10 20			
			1.65 V – 1.95 V	1.1 V – 1.3 V	5	10		
			3.0 V – 3.6 V	4.5 V – 5.5 V			1	
			1.65 V – 1.95 V	4.5 V – 5.5 V			2	
		Up Translation	1.1 V – 1.3 V	4.5 V – 5.5 V			3	
		Op Translation	1.65 V – 1.95 V	3.0 V – 3.6 V			2.5	
	Timing skew		1.1 V – 1.3 V	3.0 V – 3.6 V			3.5	
t _{sk} – Output skew	between any two switching outputs		1.1 V – 1.3 V	1.65 V – 1.95 V			4.5	no
l _{sk} – Output skew	within the same		4.5 V – 5.5 V	3.0 V – 3.6 V			1	ns
	device		4.5 V – 5.5 V	1.65 V – 1.95 V			2	
		Down Translation	4.5 V – 5.5 V	1.1 V – 1.3 V			3	
		DOWN Hansiation	3.0 V – 3.6 V	1.65 V – 1.95 V			3	
			3.0 V – 3.6 V	1.1 V – 1.3 V			4	
			1.65 V – 1.95 V	1.1 V – 1.3 V			5	

6.13 Operating Characteristics

 $T_A = 25^{\circ}C^{(1)}$

				Sı	ipply Voltage	(V _{CCB} = V _{CC}	ca)		
	PARAMETER	Test Conditions	1.2 ± 0.1V	1.5 ± 0.1V	1.8 ± 0.15V	2.5 ± 0.2V	$3.3 \pm 0.3 V$	5.0 ± 0.5V	UNIT
			TYP	TYP	TYP	TYP	TYP	TYP	
	A to B	A Port	3.5	3.7	3.9	4.2	4.5	5	
C _{pdA} (2)	B to A	CL = 0, $RL = Openf = 10$ MHz $t_{rise} = t_{fall} = 1$ ns	20.2	20.5	20.7	21.5	22.8	24.9	pF
	A to B	B Port	20.2	20.5	20.8	21.5	22.8	24.8	
C _{pdB} (2)	B to A	CL = 0, $RL = Openf = 10$ MHz $t_{rise} = t_{fall} = 1$ ns	3.5	3.7	3.9	4.2	4.5	5.1	pF

 ⁽¹⁾ See the CMOS Power Consumption and C_{pd} Calculation application report for more information about power dissipation capacitance.
 (2) C_{pdA} and C_{pdB} are respectively A-Port and B-Port power dissipation capacitances per transceiver.



6.14 Typical Characteristics

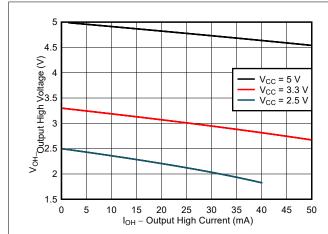


Figure 6-1. Typical (T_A =25°C) Output High Voltage (V_{OH}) vs Source Current (I_{OH})

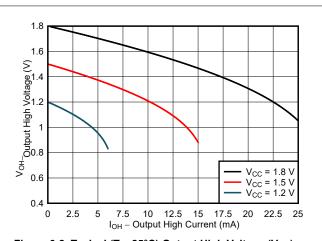


Figure 6-2. Typical (T_A =25°C) Output High Voltage (V_{OH}) vs Source Current (I_{OH})

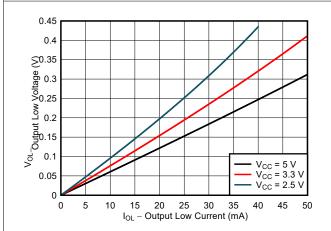


Figure 6-3. Typical (T_A =25°C) Output High Voltage (V_{OL}) vs Sink Current (I_{OL})

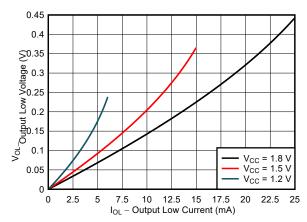


Figure 6-4. Typical (T_A =25°C) Output High Voltage (V_{OL}) vs Sink Current (I_{OL})

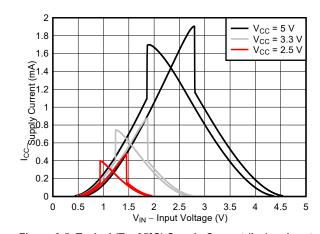


Figure 6-5. Typical (T_A =25°C) Supply Current (I_{CC}) vs Input Voltage (V_{IN})

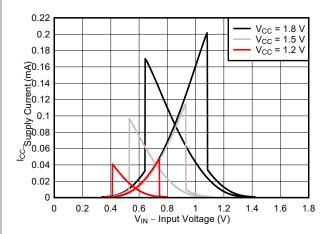


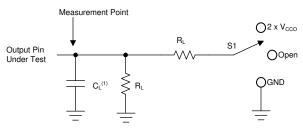
Figure 6-6. Typical (T_A =25°C) Supply Current (I_{CC}) vs Input Voltage (V_{IN})

7 Parameter Measurement Information

7.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1 MHz
- $Z_{O} = 50 \Omega$
- Δt/ΔV ≤ 1 ns/V

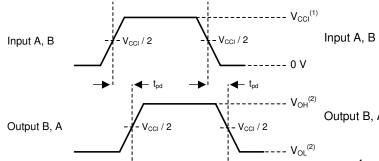


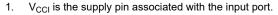
A. C_L includes probe and jig capacitance.

Figure 7-1. Load Circuit

Table 7-1. Load Circuit Conditions

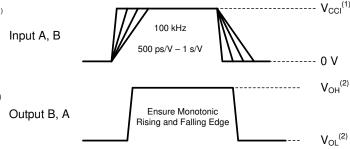
	Parameter	V _{cco}	R_L	CL	S ₁	V _{TP}
t _{pd}	Propagation (delay) time	1.1 V – 5.5 V	2 kΩ	15 pF	Open	N/A
		1.1 V – 1.6 V	2 kΩ	15 pF	2 × V _{CCO}	0.1 V
t _{en} , t _{dis}	Enable time or disable time	1.65 V – 2.7 V	2 kΩ	15 pF	2 × V _{CCO}	0.15 V
		3.0 V – 5.5 V	2 kΩ	15 pF	2 × V _{CCO}	0.3 V
		1.1 V – 1.6 V	2 kΩ	15 pF	GND	0.1 V
t _{en} , t _{dis} Enable	Enable time or disable time	1.65 V – 2.7 V	2 kΩ	15 pF	GND	0.15 V
		3.0 V – 5.5 V	2 kΩ	15 pF	GND	0.3 V





2. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L , C_L , and S_1 .

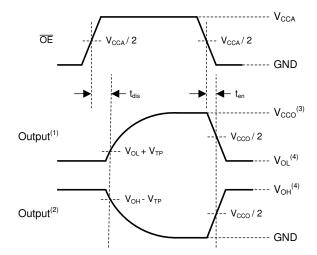
Figure 7-2. Propagation Delay



- 1. V_{CCI} is the supply pin associated with the input port.
- $m V_{OH}$ and $m V_{OL}$ are typical output voltage levels that occur with specified $m R_L$, $m C_L$, and $m S_1$.

Figure 7-3. Input Transition Rise and Fall Rate





- 1. Output waveform on the condition that input is driven to a valid Logic Low.
- 2. Output waveform on the condition that input is driven to a valid Logic High.
- 3. V_{CCO} is the supply pin associated with the output port.
- 4. V_{OH} and V_{OL} are typical output voltage levels with specified R_L , C_L , and S_1 .

Figure 7-4. Enable Time And Disable Time



8 Detailed Description

8.1 Overview

The SN74LXCH1T45 is a 1-bit translating transceiver that uses two individually configurable power-supply rails. The device is operational with V_{CCA} and V_{CCB} supplies as low as 1.1 V and as high as 5.5 V. Additionally, the device operates with $V_{CCA} = V_{CCB}$. The A port is designed to track V_{CCA} , and the B port is designed to track V_{CCB} .

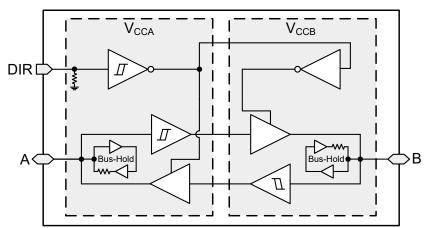
The SN74LXCH1T45 device is designed for asynchronous communication between data buses and transmits data from the A bus to the B bus or from the B bus to the A bus based on the logic level of the direction-control input (DIR). The control pin of the SN74LXCH1T45 (DIR) is referenced to V_{CCA}.

This device is fully specified for partial-power-down applications using the I_{off} current. The I_{off} protection circuitry ensures that no excessive current is drawn from or sourced into an input, output, or I/O while the device is powered down.

The V_{CC} isolation and V_{CC} disconnect feature ensures that if either V_{CC} is less than 100 mV or floating with the complementary supply within the recommended operating conditions, both I/O ports are set to the high-impedance state by disabling their outputs and the supply current is maintained.

Glitch-free power supply sequencing allows either supply rail to power on or off in any order while providing robust power sequencing performance.

8.2 Functional Block Diagram



Note: Bus-hold circuits are only present for data inputs, not control inputs

8.3 Feature Description

8.3.1 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the Electrical Characteristics. The worst case resistance is calculated with the maximum input voltage, given in the Absolute Maximum Ratings, and the maximum input leakage current, given in the Electrical Characteristics, using ohm's law $(R = V \div I)$.

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the Electrical Characteristics, which makes this device extremely tolerant to slow or noisy inputs. Driving the inputs slowly will increase dynamic current consumption of the device. See Understanding Schmitt Triggers for additional information regarding Schmitt-trigger inputs.

8.3.1.1 Control Inputs with Integrated Static Pull-Down Resistors

Similar to the data I/O's, floating control inputs can cause high current consumption. This device has integrated weak static pull-downs of $5\text{-}M\Omega$ typical on the control inputs (DIR and $\overline{\text{OE}}$) to help avoid this concern. These pull-downs are always present. For example, if the DIR pin is left floating, then the B port will be configured as an input and the A port will be configured as an output.



8.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the Absolute Maximum Ratings must be followed at all times.

8.3.3 Partial Power Down (Ioff)

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. I_{off} in the Electrical Characteristics specifies the maximum leakage into or out of any input or output pin on the device.

8.3.4 V_{CC} Isolation and V_{CC} Disconnect

The inputs and outputs for this device enter a high-impedance state when either supply is <100 mV, requiring one supply to connect to the device. Note: the bus-hold circuitry always remains active even when the device is disabled and all outputs are in the high-impedance state.

Either supply can be disconnected (floated), while the other supply is still connected and the device will maitain the maximum supply current specified by I_{CCx(floating)}, in the Electrical Characteristics. The I/O's will not enter a high-impedance state unless the supply is disconnected after it is driven to <100 mV. I_{off(float)} in the Electrical Characteristics specifies the maximum leakage into or out of any input or output pin on the device.

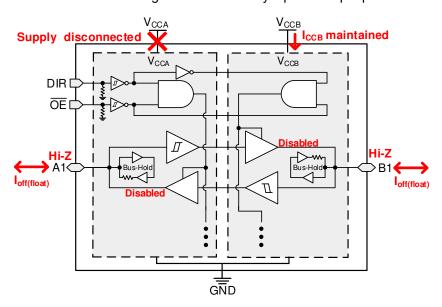


Figure 8-1. V_{CC} Disconnect Feature

8.3.5 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage as long as they remain below the maximum input voltage value specified in the Recommended Operating Conditions.

8.3.6 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

8.3.7 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 8-2.

CAUTION

Voltages beyond the values specified in Section 6.1 table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

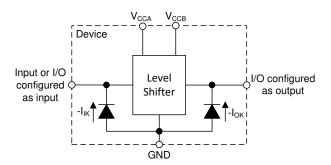


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.8 Fully Configurable Dual-Rail Design

The V_{CCA} and V_{CCB} pins can be supplied at any voltage from 1.1 V to 5.5 V, making the device suitable for translating between any of the voltage nodes (1.2 V, 1.5 V, 1.8 V, 3.3 V, and 5.0 V).

8.3.9 Supports High-Speed Translation

The SN74LXCH1T45 device can support high data-rate applications. The translated signal data rate can be up to 420 Mbps when the signal is translated from 3.3 V to 5.0 V.



8.3.10 Bus-Hold Data Inputs

Each data input on this device includes a weak latch that maintains a valid logic level on the input. The state of these latches is unknown at startup and remains unknown until the input has been forced to a valid high or low state. After data is sent through a channel, the latch maintains the previous state on the input (if the line is left floating). It is not recommended to use pull-up or pull-down resistors together with a bus-hold input, as it may cause undefined inputs to occur which leads to excessive current consumption.

Bus-hold data inputs prevent floating inputs on this device. The Implications of Slow or Floating CMOS Inputs application report explains the problems associated with leaving the CMOS inputs floating. These latches remain active at all times, independent of all control signals such as direction control or output enable. The latches also remain active when the device is in the partial power down state, corresponding supply is still present, or when the I/O's are floated. The Bus-Hold Circuit application report has additional details regarding bus-hold inputs.

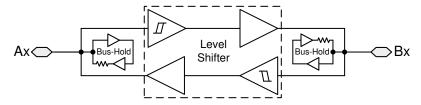


Figure 8-3. Schematic Description of Location of Bus-Hold Circuits

8.4 Device Functional Modes

Table 8-1. Function Table⁽¹⁾

CONTROL INPL	JTS	PORT S	TATUS	OPERATION
ŌĒ	DIR	A PORT	B PORT	OPERATION
L	L	Output (Enabled)	Input (Hi-Z)	B data to A bus
L	Н	Input (Hi-Z)	Output (Enabled)	A data to B bus
Н	X	Input (Hi-Z)	Input (Hi-Z)	Isolation

(1) Input circuits of the data I/Os are always active.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LXCH1T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74LXCH1T45 device is ideal for use in applications where a push-pull driver is connected to the data I/O. The maximum data rate can be up to 420 Mbps when the device translates a signal from 3.3 V to 5.0 V.

9.2 Enable Times

Calculate the enable times for the SN74LXCH1T45 using the following formulas:

$$t_{A en}$$
 (DIR to A) = t_{dis} (DIR to B) + t_{pd} (B to A) (1)

$$t_{B \text{ en}}$$
 (DIR to B) = t_{dis} (DIR to A) + t_{pd} (A to B) (2)

In a bidirectional application, these enable times provide the maximum delay time from the time the DIR bit is switched until an output is expected. For example, if the SN74LXCH1T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled (t_{dis}) before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay (t_{pd}) . To avoid bus contention, care should be taken to not apply an input signal prior to the output being disabled (t_{dis}) maximum.

9.3 Typical Application

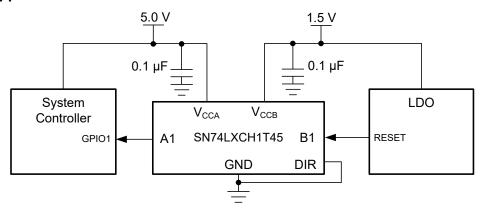


Figure 9-1. LED Driver Application

9.3.1 Design Requirements

Use the parameters listed in Table 9-1 for this design example.

Table 9-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.1 V to 5.5 V
Output voltage range	1.1 V to 5.5 V



9.3.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range:
 - Use the supply voltage of the device that is driving the SN74LXCH1T45 device to determine the input voltage range. The value must exceed the high-level input voltage (V_{IH}) of the input port for a valid logic-high. The value must be less than the low-level input voltage (V_{IL}) of the input port for a valid logic low.
- Output voltage range:
 - Use the device's supply voltage that the SN74LXCH1T45 device is driving to determine the output voltage range.

9.3.3 Application Curve

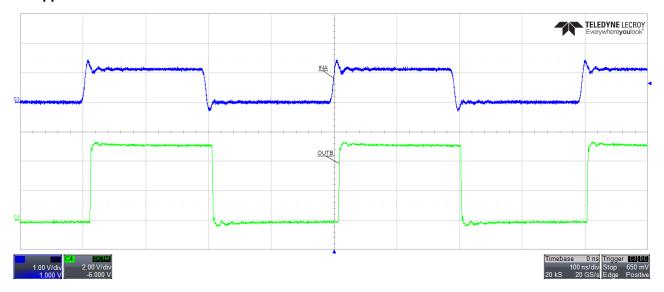


Figure 9-2. Up Translation at 2.5 MHz (1.2 V to 5 V)

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10 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

Section 8.3.6 describes how this device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices.

11 Layout

11.1 Layout Guidelines

Following common printed-circuit board layout guidelines are recommended to ensure reliability of the device, which follows:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1 μF capacitor is recommended, but transient performance can be improved by having both 1 μF and 0.1 μF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads; so routing and load conditions should be considered to prevent ringing.

11.2 Layout Example

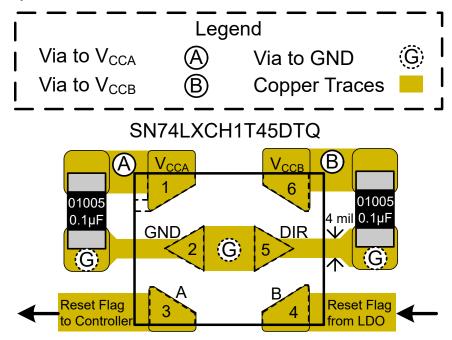


Figure 11-1. Layout Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application report
- Texas Instruments, Semiconductor and IC Package Thermal Metrics appliction report
- Texas Instruments, System Considerations for Using Bus-Hold Curcuits to Avoid Floating Inputs application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74LXCH1T45DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	2NNT	Samples
SN74LXCH1T45DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MJ	Samples
SN74LXCH1T45DTQR	ACTIVE	X2SON	DTQ	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MF	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LXCH1T45DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LXCH1T45DRYR	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1
SN74LXCH1T45DTQR	X2SON	DTQ	6	3000	180.0	9.5	0.94	1.13	0.5	2.0	8.0	Q2

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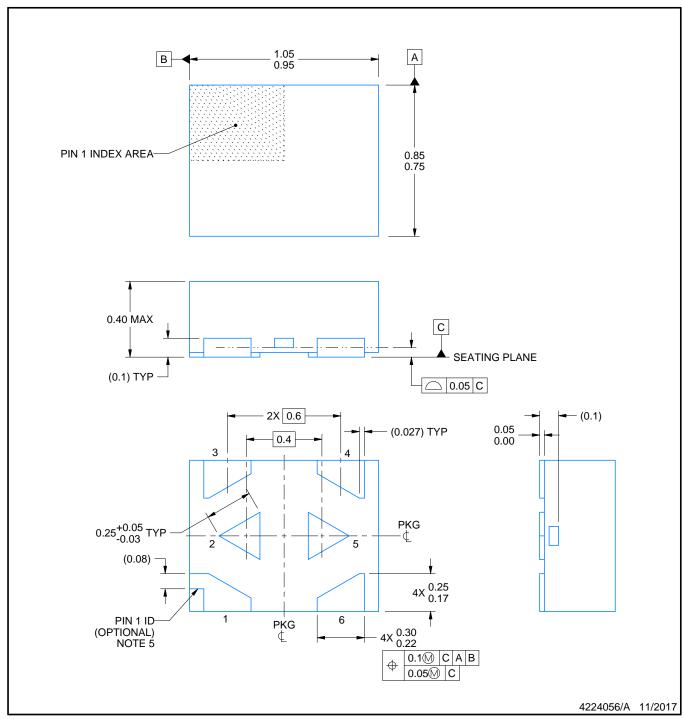


*All dimensions are nominal

7 till difficilities are fremmal								
Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
SN74LXCH1T45DCKR	SC70	DCK	6	3000	180.0	180.0	18.0	
SN74LXCH1T45DRYR	SON	DRY	6	5000	189.0	185.0	36.0	
SN74LXCH1T45DTQR	X2SON	DTQ	6	3000	189.0	185.0	36.0	



PLASTIC SMALL OUTLINE - NO LEAD



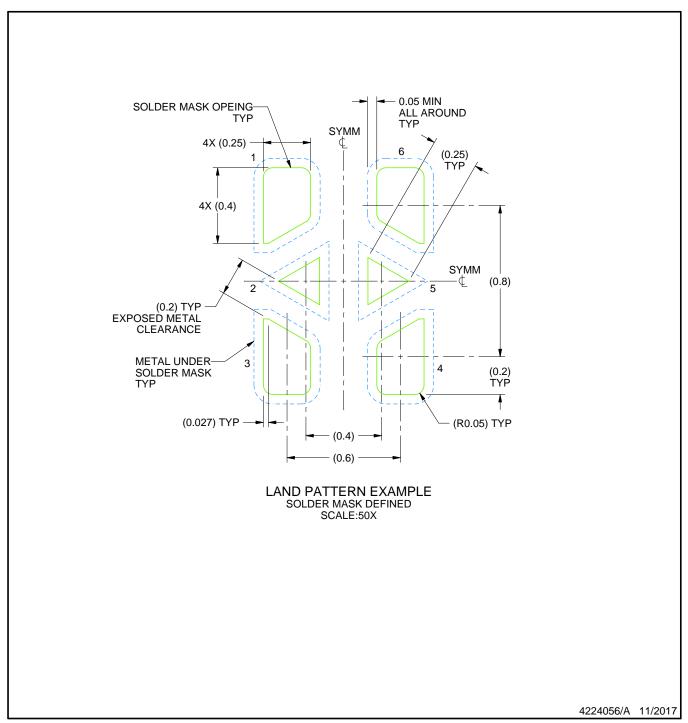
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.

 4. The size and shape of this feature may vary.
- 5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.



PLASTIC SMALL OUTLINE - NO LEAD



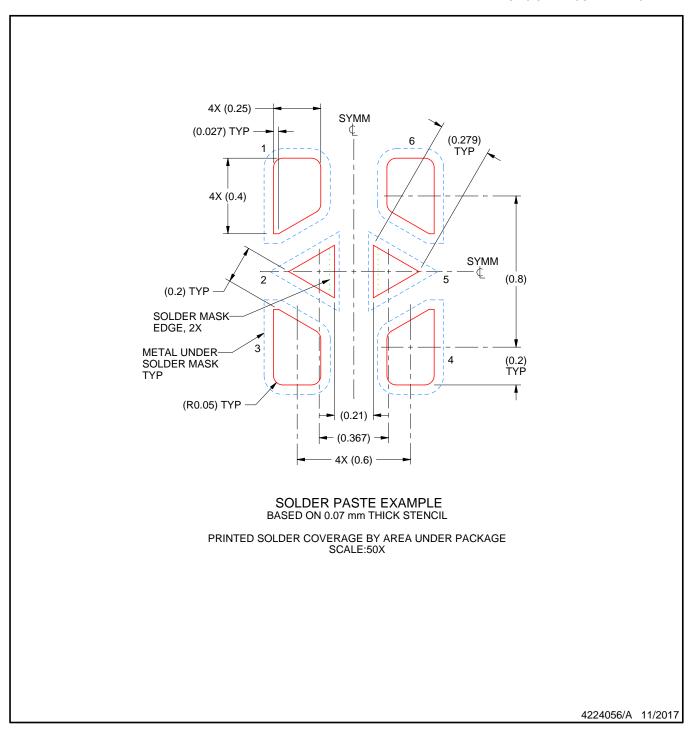
NOTES: (continued)



^{6.} This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

^{7.} Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





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